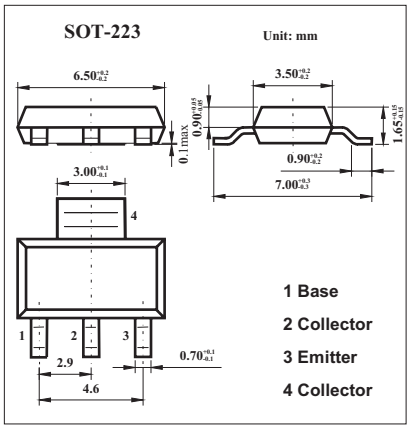
PNP High-Voltage Transistor

BSP16



Features

- High voltage (max. 350 V).

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
collector-base voltage (open emitter)	V_{CBO}	-350	V
collector-emitter voltage (open base)	V_{CEO}	-300	V
emitter-base voltage (open collector)	V_{EBO}	-6	V
collector current (DC)	I_C	-200	mA
base current (DC)	I_B	-200	mA
total power dissipation $T_{amb} \leqslant 25$ ℃ *	P_{tot}	1.28	W
storage temperature	T_{stg}	-65 to 150	℃
junction temperature	T_j	150	℃
operating ambient temperature	T_{amb}	-65 to 150	℃
thermal resistance from junction to ambient *	Rth j-a	97	K/W
thermal resistance from junction to soldering point	Rth j-s	16	K/W

* . Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm^2.

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
collector cut-off current	I_{CBO}	I_E = 0; V_{CB} = -280 V			-100	nA
emitter cut-off current	I_{EBO}	I_C = 0; V_{EB} = -6 V			-100	nA
DC current gain	h_{FE}	I_C = -50 mA; V_{CE} = -10 V	30		120	
collector-emitter saturation voltage	V_{CEsat}	I_C = -50 mA; I_B = -5 mA			-2	V
collector capacitance	C_c	$I_E = i_e$ = 0; V_{CB} = -10 V; f = 1 MHz			15	pF
transition frequency	f_T	I_C = -10 mA; V_{CE} = -10 V; f = 100 MHz	15			MHz